Modulation of electronic properties in two-dimensional platinum chalcogenides

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Among layered materials, platinum chalcogenides have received great attention due to their peculiar physical properties. The strong layer-dependent electronic properties cause a band gap opening in monolayer PtTe₂, while the system otherwise is (semi)metallic.[1] Here we show that starting with PtTe₂ films, other compositions such as Pt₃Te₄ and Pt₂Te₂ can be obtained by a postgrowth desorption of tellurium or vapor-deposited Pt atoms.[2] The experiments combined with DFT calculations provide insights into these transformation mechanisms and the stabilization of the new phases. The partially converted monolayer flakes exhibit PtTe₂-Pt₂Te₂ heterojunctions, which enable the formation of the in-plane semiconductor-metal interface.[3] We further studied the electronic structure of edges and point defects in PtSe₂ monolayer where metallic 1D states with spin-polarized bands were found.[4] In addition to stoichiometry, combining different Pt-chalcogenides in vertical heterostructures provides an additional degree of engineering of materials properties. [5] Our results showed the variation of the interlayer interaction within the moiré structure locally modulates the electronic structure of PtSe₂/PtTe₂ heterostructures.

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